

STANDARD RECOVERY DIODES

- Junction Size: Square 230 mils
- Wafer Size: 4"
- V_{RRM} Class: 1200 V
- Passivation Process: Glassivated MOAT
- Reference IR Packaged Part: 40EPS Series

Major Ratings and Characteristics

Parameters	Units	Test Conditions
V_{FM} Maximum Forward Voltage	1050 mV	$T_J = 25^\circ\text{C}$, $I_F = 20\text{ A}$
V_{RRM} Reverse Breakdown Voltage	1200 V	$T_J = 25^\circ\text{C}$, $I_{RRM} = 100\text{ }\mu\text{A}$ (1)

(1) Nitrogen flow on die edge.

Mechanical Characteristics

Nominal Back Metal Composition, Thickness	Cr - Ni - Ag (1 KA - 4 KA - 6 KA)
Nominal Front Metal Composition, Thickness	100% Al, (20 μm)
Chip Dimensions	230 x 230 mils (see drawing)
Wafer Diameter	100 mm, with std. < 110 > flat
Wafer Thickness	300 μm , $\pm 10\text{ }\mu\text{m}$
Maximum Width of Sawing Line	45 μm
Reject Ink Dot Size	0.25 mm diameter minimum
Ink Dot Location	See drawing
Recommended Storage Environment	Storage in original container, in dessicated nitrogen, with no contamination

IR230DM12CCB

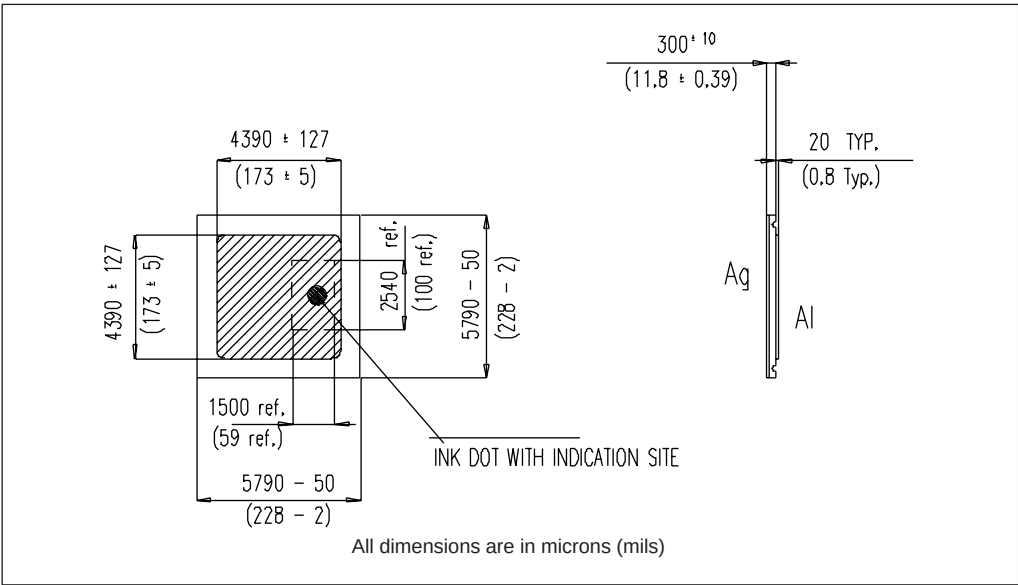
Bulletin I0121J rev. A 02/97

International
IR Rectifier

Ordering Information Table

Device Code						
IR	230	D	M	12	C	CB
①	②	③	④	⑤	⑥	⑦
1	- International Rectifier Device					
2	- Chip Dimension in Mils					
3	- Type of Device: D = Wire Bondable Standard Recovery Diode					
4	- Passivation Process: M = Glassivated MOAT					
5	- Voltage code: Code x 100 = V_{RRM}					
6	- Metallization: C = Aluminium (Anode) - Silver (Cathode)					
7	- CB = Probed Uncut Die (wafer in box) None = Probed Die in chip carrier					

Outline Table



Wafer Layout

